

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM} V_{RRM}$	600 / 800	V
V_{TM}	1.55	V

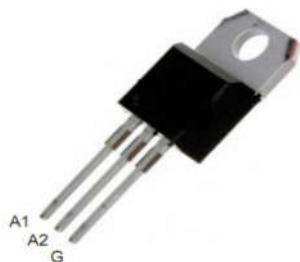
Feature

With high ability to withstand the shock loading of large current, With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

Application

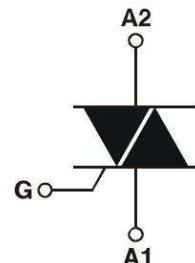
Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

Package

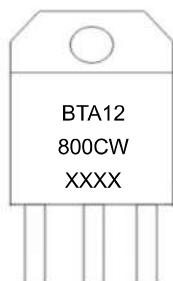


TO-220A Insulated

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value		Unit
Repetitive peak off-state voltage	V _{DRM}	600 / 800		V
Repetitive peak reverse voltage	V _{RRM}	600 / 800		V
RMS on-state current	I _{T(RMS)}	12		A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I _{TSM}	120		A
I ² t value for fusing (tp=10ms)	I ² t	78		A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT})	dI _T /dt	I - II - III	50	A/μs
Peak gate current	I _{GM}	4		A
Average gate power dissipation	P _{G(AV)}	1		W
Junction Temperature	T _J	-40 ~ +125		°C
Storage Temperature	T _{STG}	-40 ~ +150		°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value		Unit
			SW	CW	
Gate trigger current	I _{GT}	V _D =12V R _L = 33Ω T _j =25°C	I - II - III	≤10	≤35
Gate trigger voltage	V _{GT}		I - II - III	≤1.3	V
Gate non-trigger voltage	V _{GD}	V _D =V _{DRM} T _j =125°C	≥0.2		
latching current	I _L	I _G =1.2I _{GT}	I - III	≤25	≤50
			II	≤30	≤60
Holding current	I _H	I _T =100mA	≤15	≤35	mA
Critical-rate of rise of commutation voltage	dV _D /dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	≥40	≥500	V/μs

STATIC CHARACTERISTICS

Forward "on" voltage	V _{TM}	I _{TM} =17A tp=380μs	≤1.55	V
Repetitive Peak Off-State Current	I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	≤5
Repetitive Peak Reverse Current	I _{RRM}		T _j =125°C	≤1

THERMAL RESISTANCES

Thermal resistance	R _{th(j-c)}	Junction to case(AC)	2.3	°C/W
	R _{th(j-a)}	Junction to ambient	60	°C/W

Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

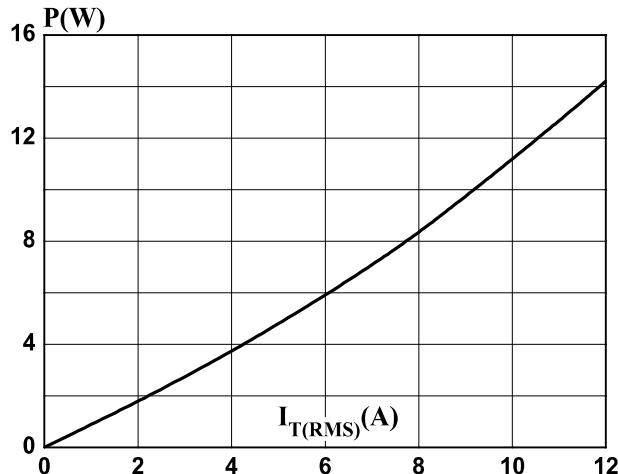


FIG.2: RMS on-state current versus case temperature (full cycle)

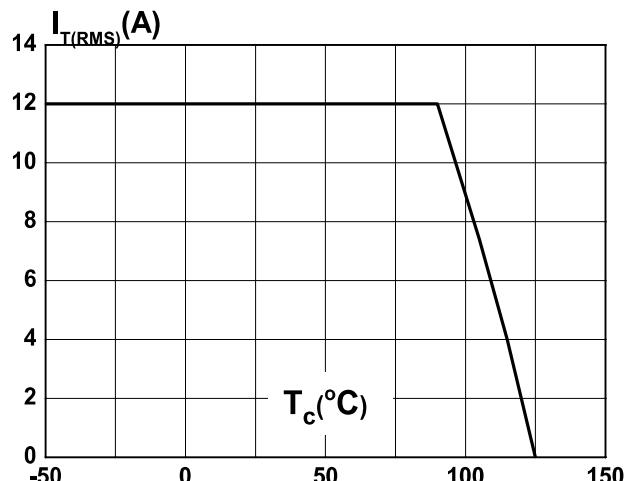


FIG.3: Surge peak on-state current versus number of cycles

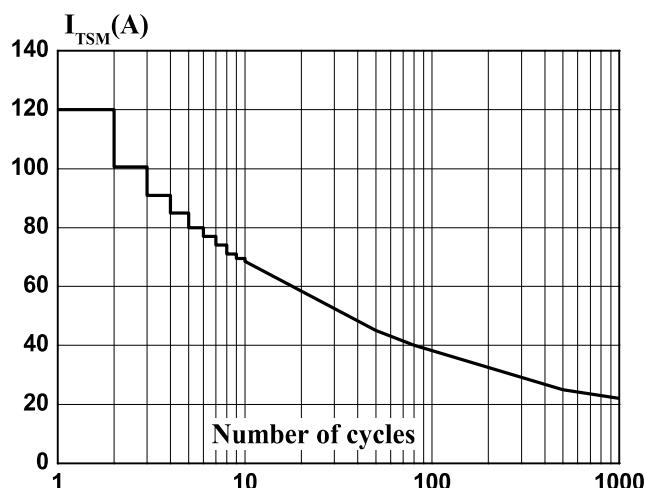


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

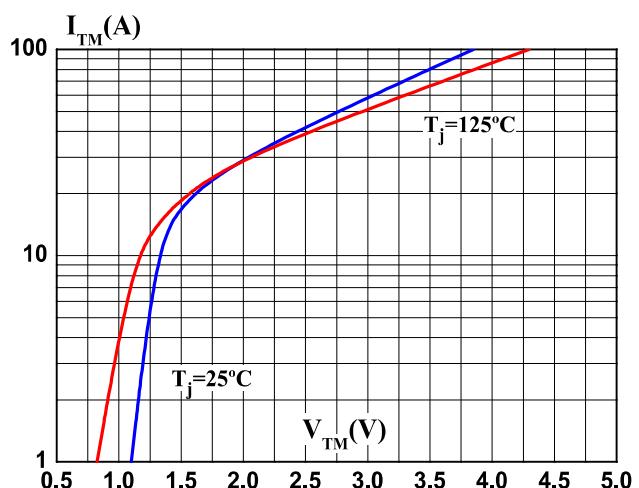
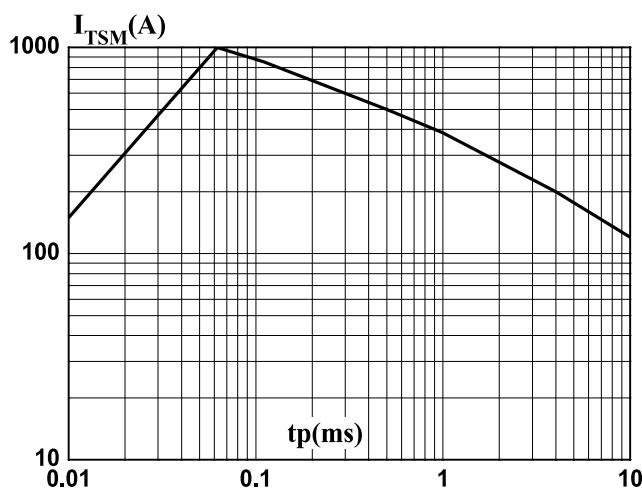
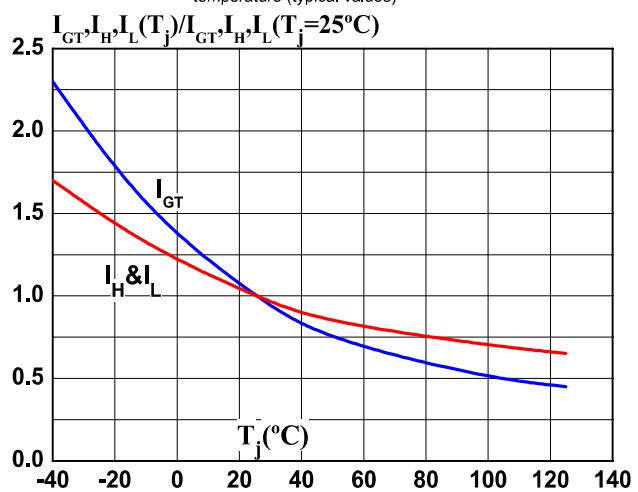


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Ordering Information

BT <small>Triacs</small>	A <small>A: TO-220A Insulated</small>	12	800	C <small>C:I_{GT1-3} ≤ 35mA S:I_{GT1-3} ≤ 10mA</small>	W <small>W: 3Q</small>
<small>I_{T(RMS)}: 12A</small>				<small>600: V_{DRM} / V_{RRM} ≥ 600V 800: V_{DRM} / V_{RRM} ≥ 800V</small>	

TO-220A Insulated Package Information

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.8	10.4	0.385	0.409
B	2.65	3.1	0.104	0.122
C	2.8	4.2	0.110	0.165
D	0.7	0.92	0.027	0.036
E	3.75	3.95	0.147	0.155
F	14.8	16.1	0.582	0.633
G	13.05	13.6	0.513	0.535
H	2.4	2.7	0.094	0.106
I	4.38	4.61	0.172	0.181
J	1.15	1.36	0.045	0.053
K	5.85	6.82	0.230	0.268
L	2.35	2.75	0.092	0.108
M	0.35	0.65	0.013	0.025
N	1.18	1.42	0.046	0.055